IN THE SPECIFICATION

Following is a marked-up version of each amended paragraph of the subject patent application. The Examiner is requested to delete the indicated paragraph and replace it with the amended paragraph. The paragraph number for each amended paragraph is indicated.

Replace paragraph [0004] with the following.

[0004] An intermetal dielectric layer 40 is formed over an upper surface 42 of the silicon substrate 10, followed by formation of windows 44 extending through the intermetal dielectric layer 40 to the device regions that are to be connected to other active regions formed in the substrate 10. The windows 44 are formed ~~of rmed~~ using known photolithographic masking, patterning and etching processes. Tungsten plugs, formed within the windows 44 as described below, interconnect the device regions to an overlying interconnect layer formed later overlying the upper surface of the intermetal dielectric layer 40.

Replace paragraph [0021] with the following.

[0021] A magnet 118 creates a magnetic field that generally confines the argon plasma to a region 119 where the increased plasma density improves the sputtering efficiency. As the argon ions 116 strike the target 102, the momentum of the ions is transferred to the atoms of the target material, sputtering or knocking the atoms from the target 102. A high density of argon ions 116 in the chamber 100 ensures that a significant number of sputtered atoms condense on~~f~~ the upper surface of the wafer 106. The target material is thus deposited on the wafer 106 without undergoing any chemical or compositional changes. The various sputtering chamber parameters, including chamber pressure, chamber and wafer temperature, deposition power (i.e., the power supplied to the target 102 by the power supply 110, where power is the product of voltage and current) can be varied to achieve the desired characteristics in the sputtered film. Layers of different materials can also be sputtered in a single process using multiple target arrangements.